



### **IRLU7843-701PBF Information**



For Reference Only

Part Number IRLU7843-701PBF
Manufacturer Infineon Technologies

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 30V 161A IPAK

Package TO-251-3 Short Leads, IPak, TO-251AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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## **IRLU7843-701PBF Specifications**

Manufacturer Part Number         IRLU7843-701PBF           Manufacturer         Infineon Technologies           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-251-3 Short Leads, IPak, TO-251AA           Series         HEXFET?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         30V           Current - Continuous Drain (Id) @ 25°C         161A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         2.3V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         50nC @ 4.5V           Input Capacitance (Ciss) (Max) @ Vds         4380pF @ 15V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         140W (Tc)           Rds On (Max) @ Id, Vgs         3.3 mOhm @ 15A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         I-Pak           Package / Case         TO-251-3 Short Leads, IPak, TO-251AA		
CategoryDiscrete Semiconductor ProductsFackageTO-251-3 Short Leads, IPak, TO-251AASeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C161A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.3V @ 250μAGate Charge (Qg) (Max) @ Vgs50nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds4380pF @ 15VVgs (Max)±20VFET Feature-Power Dissipation (Max)140W (Tc)Rds On (Max) @ Id, Vgs3.3 mOhm @ 15A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device Package1-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Manufacturer Part Number	IRLU7843-701PBF
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FET Type  Rochannel  Technology  MOSFET (Metal Oxide)  MOSFET (Metal Oxide)  30V  Current - Continuous Drain (Id) @ 25°C  161A (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Cate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Supplier Device Package  Package / Case  N-Channel  MOSFET (Metal Oxide)  MOSFET (Metal Oxide)  30V  AUSFET (Metal Oxide)  30V  161A (Tc)  161A (Tc)	Package	TO-251-3 Short Leads, IPak, TO-251AA
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C161A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.3V @ 250μAGate Charge (Qg) (Max) @ Vgs50nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds4380pF @ 15VVgs (Max)±20VFET Feature-Power Dissipation (Max)140W (Tc)Rds On (Max) @ Id, Vgs3.3 mOhm @ 15A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Series	HEXFET?
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Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  2.3V @ 250μA  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  3.3 mOhm @ 15A, 10V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  Package / Case  TO-251-3 Short Leads, IPak, TO-251AA	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Through Hole  Supplier Device Package  Package / Case  2.3V @ 250μA	Current - Continuous Drain (Id) @ 25°C	161A (Tc)
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FET Feature -  Power Dissipation (Max) 140W (Tc)  Rds On (Max) @ Id, Vgs 3.3 mOhm @ 15A, 10V  Operating Temperature -55°C ~ 175°C (TJ)  Mounting Type Through Hole  Supplier Device Package I-Pak  Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Input Capacitance (Ciss) (Max) @ Vds	4380pF @ 15V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  3.3 mOhm @ 15A, 10V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  I-Pak  Package / Case  TO-251-3 Short Leads, IPak, TO-251AA	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs3.3 mOhm @ 15A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	FET Feature	-
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Supplier Device Package  I-Pak Package / Case  TO-251-3 Short Leads, IPak, TO-251AA	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Mounting Type	Through Hole
	Supplier Device Package	I-Pak
Report errors?	Package / Case	TO-251-3 Short Leads, IPak, TO-251AA
		Report errors?

### **IRLU7843-701PBF Guarantees**



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

# **IRLU7843-701PBF Payment Methods**





















## **IRLU7843-701PBF Shipping Methods**













If you have any question about IRLU7843-701PBF, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com